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1765

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the Patent Application of

Seichi FUKUDA

Serial No. 09/512,336

Filed: February 24, 2000

For: DRY ETCHING METHOD AND  
METHOD OF MANUFACTURING  
SEMICONDUCTOR APPARATUS

Group Art Unit: 1765

Examiner: K. Chen

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 AUG 20 2001  
 TC 1700
#7BME  
8/20/01  
MLW

COMMISSIONER FOR PATENTS

BOX AF

Washington, D.C. 20231

Sir:

Transmitted herewith is an amendment in the above-identified application.

☒ No additional fee is required.

The fee has been calculated as shown below

## CLAIMS AS AMENDED

	CLAIMS REMAINING AFTER AMENDMENT		HIGHEST NO. PREVIOUSLY PAID FOR	PRESENT EXTRA	RATE	ADDITIONAL FEE
TOTAL CLAIMS	8	MINUS	20	=0	x \$9 \$18	\$0.00
INDEP. CLAIMS	2	MINUS	3	=0	x\$40 \$80	\$0.00
Fee for Multiple Dependent Claims \$130/\$260						
				TOTAL ADDITIONAL FEE FOR THIS AMEND- MENT	\$0.00	

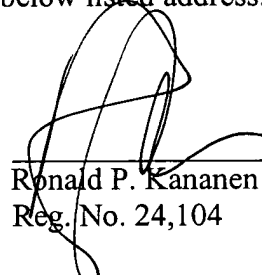
- If the entry in Column 2 is less than the entry in Column 4,
  - write "0" in Column 5.
- If the "Highest Number Previously Paid For" IN THIS SPACE is less than 20, write "20" in this space.
- If the "Highest Number Previously Paid For" IN THIS SPACE is less than 3, write "3" in this space.

- ☐ A Letter to the Official Draftsperson is enclosed.
- ☐ A Change of Address is enclosed.
- ☐ Charge \$\_\_\_\_\_ to Deposit Account No. 18-0013. A duplicate copy of this sheet is enclosed.
- ☒ Any prior general authorization to charge an issue fee under 37 C.F.R. 1.18 to Deposit Account No. 18-0013 is hereby revoked. The Commissioner is hereby authorized to charge any additional fees under 37 CFR 1.16 and 1.17 which may be required during the entire pendency of this application, or to credit any overpayment, to Deposit Account No. 18-0013. A duplicate copy of this sheet is enclosed.
- ☐ Charge \$\_\_\_\_\_ to Deposit Account No. 18-0013 to cover the Extension fee for response within \_\_\_\_\_ month(s).
- ☒ Applicant's undersigned attorney may be reached by telephone in our Washington D.C. Office at

(202) 955-3750.

All correspondence should be directed to our below listed address.

Date: 16 August 2001

  
\_\_\_\_\_  
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AMENDMENT AFTER FINAL OFFICE ACTION UNDER RULE 116

Commissioner of Patents

**BOX AF**

Washington, DC 20231

Sir:

In response to the final Official Action mailed June 21, 2001 (Paper No. 6), please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend the claims as shown in the Appendix. The claims as amended are presented immediately herebelow.

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B1

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1. (amended) A dry etching method comprising the step of:  
dry-etching tungsten using only a single mixed gas  
including a fluorine-containing gas that includes a compound  
having fluorine and carbon in a molecule, chlorine or hydrogen  
bromide, oxygen, and nitrogen.

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